

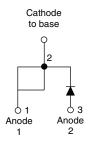
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 8 A



TO-247AC modified



PRODUCT SUMMARY							
Package	TO-247AC modified (2 pins)						
I _{F(AV)}	8 A						
V_{R}	1200 V						
V _F at I _F	2.4 V						
t _{rr} typ.	28 ns						
T _J max.	150 °C						
Diode variation	Single die						

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA08PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V_R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	8						
Single pulse forward current	I _{FSM}		130	Α					
Maximum repetitive forward current	I _{FRM}		32						
Maximum navvey discination	Б	T _C = 25 °C	73.5	W					
Maximum power dissipation	P_{D}	T _C = 100 °C	29] vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					



leakage current

Junction capacitance

Series inductance

VS-HFA08PB120PbF, VS-HFA08PB120-N3

See fig. 3

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135

11

8.0

1000

20

pF

nΗ

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified) SYMBOL **PARAMETER TEST CONDITIONS UNITS** MIN. TYP. MAX. Cathode to anode V_{BR} $I_R = 100 \mu A$ 1200 breakdown voltage $I_F = 8.0 A$ 2.6 3.3 ٧ I_F = 16 A See fig. 1 4.3 Maximum forward voltage 3.4 V_{FM} $I_F = 8.0 \text{ A}, T_J = 125 \, ^{\circ}\text{C}$ 2.4 3.1 $V_R = V_R$ rated 0.31 10 Maximum reverse I_{RM} See fig. 2

Measured lead to lead 5 mm from package body

 $T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated

 $V_{R} = 200 V$

Ст

 L_S

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	-	28	-					
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	63	95	ns			
000 lig. 0, 10	t _{rr2}	T _J = 125 °C		-	106	160				
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	A nC A/μs			
	I _{RRM2}	T _J = 125 °C		-	6.2	11				
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380				
See fig. 7	Q _{rr2}	T _J = 125 °C		-	335	880				
Peak rate of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	-				
	dI _{(rec)M} /dt2	T _J = 125 °C		-	85	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-					
Weight			-	6.0	-	g				
vveignt			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC modified (JEDEC)	HFA08PB120			•				

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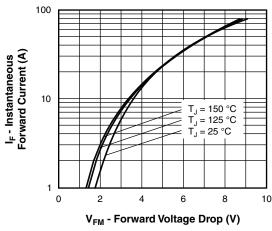


Fig. 1 - Maximum Forward Voltage Drop Characteristics

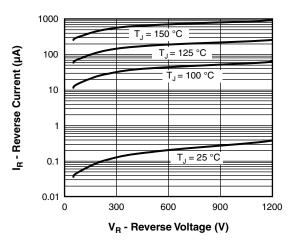


Fig. 2 - Values of Reverse Current vs. Reverse Voltage

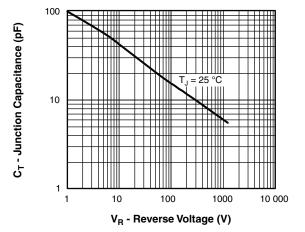


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

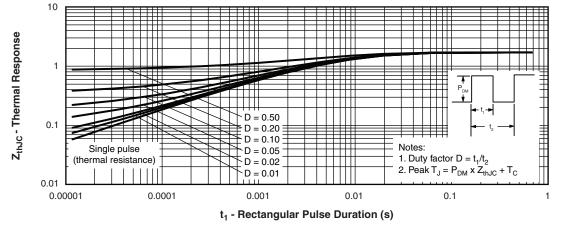


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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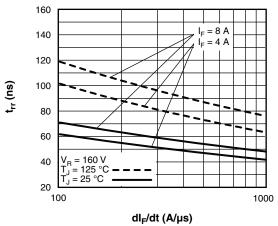


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

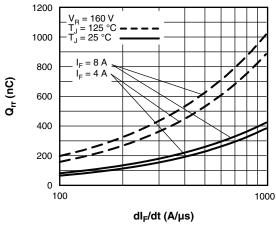


Fig. 7 - Typical Stored Charge vs. dl_F/dt

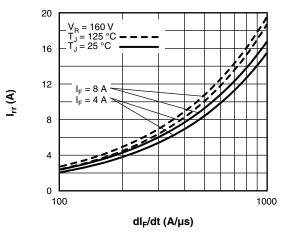


Fig. 6 - Typical Recovery Current vs. dl_F/dt

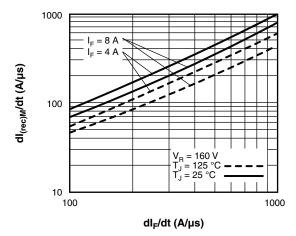


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

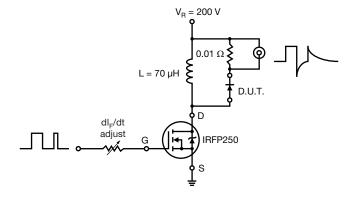
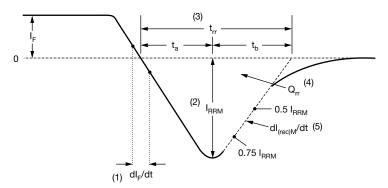


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA08PB120PbF, VS-HFA08PB120-N3

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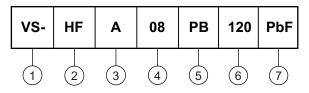


- (1) dl_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and l_{RRM}
- (2) I_{RBM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{r}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- 3 Electron irradiated
- 4 Current rating (08 = 8A)
- 5 PB = TO-247AC modified
- Voltage rating: (120 = 1200 V)
- 7 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

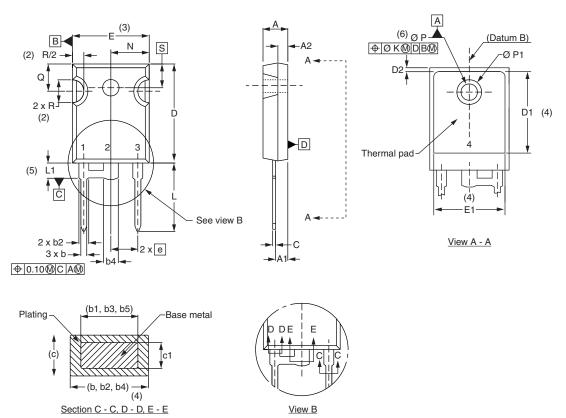
ORDERING INFORMATION (Example)									
PREFERRED P/N	EFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-HFA08Pb120PbF	25	500	Antistatic plastic tube						
VS-HFA08Pb120-N3	25	500	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95541						
Port marking information	TO-247AC modified PbF	www.vishay.com/doc?95255						
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442						

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TO-247 - 50 mils L/F modified

DIMENSIONS in millimeters and inches



CVMDOL	MILLIMETERS		METERS INCHES		NOTES	NOTES	CVMDOL	MILLIM	METERS	INC	HES	NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	, IES	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØK	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	'BSC	

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

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Revision: 02-Oct-12 Document Number: 91000